

TC7W53FK : UNDER DEVELOPMENT

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W53F, TC7W53FU, TC7W53FK

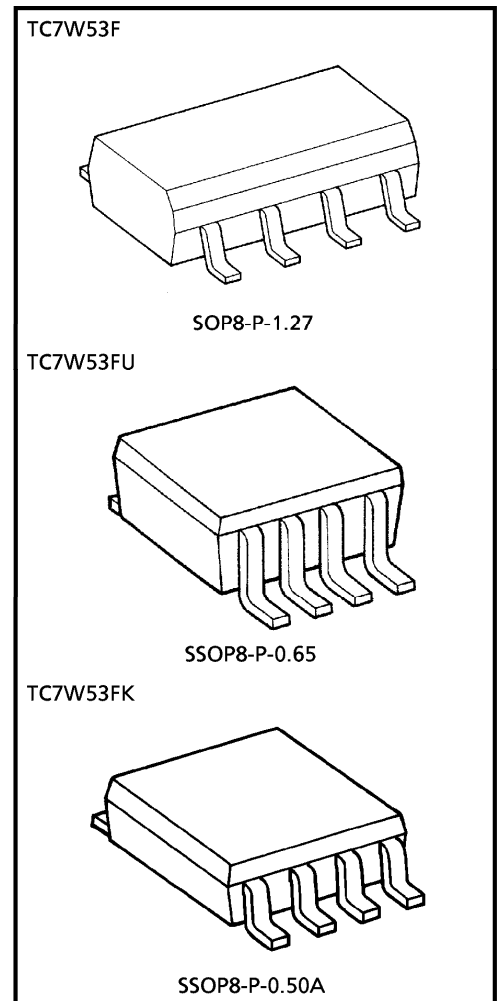
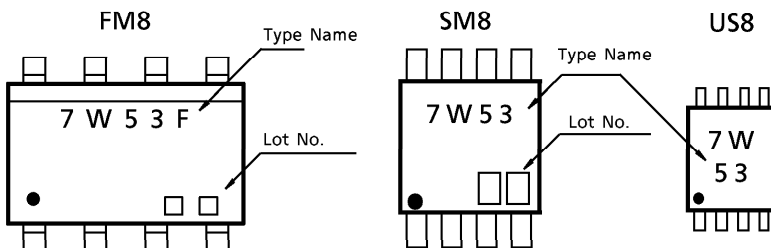
2-CHANNEL MULTIPLEXER / DEMULTIPLEXER

The TC7W53 is a high speed CMOS ANALOG MULTIPLEXER/DEMULTIPLEXER fabricated with silicon gate CMOS technology. They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. The TC7W53 has a 2 channel configuration. The digital signal to the control terminal turns "ON" the corresponding switch of each channel a large amplitude signal ($V_{CC}-V_{EE}$) can then be switched by the small logical amplitude ($V_{CC}-GND$) control signal. For example, in the case of $V_{CC} = 5V$, $GND = 0V$, $V_{EE} = 5V$, signals between $-5V$ and $+5V$ can be switched from the logical circuit with a single power supply of 5V. As the ON-resistance of each switch is low, they can be connected to circuit with low input impedance. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

- High Speed $t_{pd} = 15ns$ (Typ.)
at $V_{CC} = 5V$, $V_{EE} = 0V$
- Low Power Dissipation $I_{CC} = 4\mu A$ (Max.) at $T_a = 25^\circ C$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Low ON Resistance $R_{ON} = 50\Omega$ (Typ.)
at $V_{CC}-V_{EE} = 9V$
- High Degree of Linearity $THD = 0.02$ (Typ.)
at $V_{CC}-V_{EE} = 9V$
- Pin and Function Compatible with TC4W53

MARKING



Weight

SOP8-P-1.27	: 0.05g (Typ.)
SSOP8-P-0.65	: 0.02g (Typ.)
SSOP8-P-0.50A	: 0.01g (Typ.)

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MAXIMUM RATINGS (Ta = 25°C)

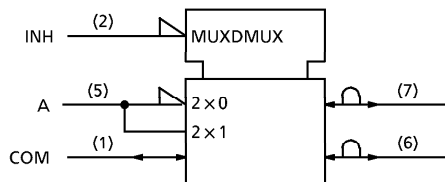
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	-0.5~7	V
	V _{CC} ~V _{EE}	-0.5~13	
Control Input Voltage	V _{IN}	-0.5~V _{CC} +0.5	V
Switch I/O Voltage	V _{I/O}	V _{EE} -0.5~V _{CC} +0.5	V
Control Input Diode Current	I _{CK}	±20	mA
I/O Diode Current	I _{I/O}	±20	mA
Switch Through Current	I _T	±25	mA
DC V _{CC} /GND Current	I _{CC}	±25	mA
Power Dissipation	P _D	300 (FM8, SM8)	mW
		200 (US8)	
Storage Temperature	T _{stg}	-65~150	°C
Lead Temperature (10 s)	T _L	260	°C

TRUTH TABLE

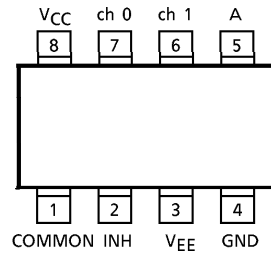
CONTROL INPUT		ON CHANNEL
INH	A	
L	L	ch 0
L	H	ch 1
H	x	NONE

x : Don't care

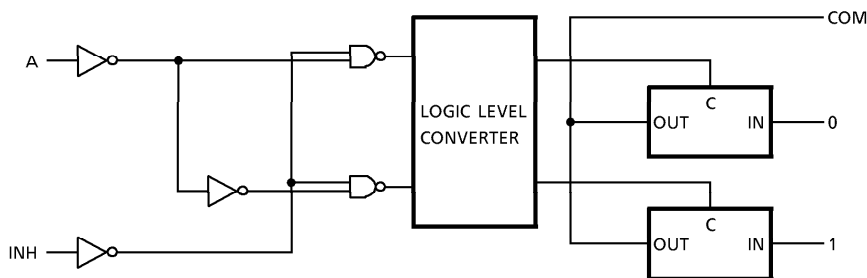
LOGIC SYMBOL



PIN ASSIGNMENT (TOP VIEW)



LOGIC DIAGRAM



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2~6	V
	V_{EE}	-6~0	V
	$V_{CC} \sim V_{EE}$	2~12	V
Control Input Voltage	V_{IN}	0~ V_{CC}	V
Switch I/O Voltage	$V_{I/O}$	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0V$)	ns
		0~500 ($V_{CC} = 4.5V$)	
		0~400 ($V_{CC} = 6.0V$)	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL		V_{EE} (V)	V_{CC} (V)	$T_a = 25^\circ C$			$T_a = -40 \sim 85^\circ C$		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Control Input Voltage	V_{IHC}			2.0	1.5	—	—	1.5	—	V
				4.5	3.15	—	—	3.15	—	
				6.0	4.2	—	—	4.2	—	
Low-Level Control Input Voltage	V_{ILC}			2.0	—	—	0.5	—	0.5	V
				4.5	—	—	1.35	—	1.35	
				6.0	—	—	1.8	—	1.8	
ON Resistance	R_{ON}	$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ to GND $V_{I/O} \leq 2mA$	GND	4.5	—	85	180	—	225	Ω
			-4.5	4.5	—	55	120	—	150	
			-6.0	6.0	—	50	100	—	125	
		$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ or GND $V_{I/O} \leq 2mA$	GND	2.0	—	150	—	—	—	
			GND	4.5	—	70	150	—	190	
			-4.5	4.5	—	50	100	—	125	
Difference of ON Resistance Between Switches	ΔR_{ON}	$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ to GND $V_{I/O} \leq 2mA$	GND	4.5	—	10	30	—	35	Ω
			-4.5	4.5	—	5	12	—	15	
			-6.0	6.0	—	5	10	—	12	
Input/Output Leakage Current (SWITCH OFF)	I_{OFF}	$V_{OS} = GND$ $V_{IS} = GND$ to V_{CC} $V_{IN} = V_{ILC}$ or V_{IHC}	GND	6.0	—	—	± 60	—	± 600	nA
			-6.0	6.0	—	—	± 100	—	± 1000	
Switch Input Leakage Current (SWITCH ON OUTPUT OPEN)	I_{IZ}	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{ILC}$ or V_{IHC}	GND	6.0	—	—	± 60	—	± 600	nA
			-6.0	6.0	—	—	± 100	—	± 1000	
Control Input Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	GND	6.0	—	—	± 0.1	—	± 1.0	μA
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	GND	6.0	—	—	4	—	40	μA
			-6.0	6.0	—	—	8	—	80	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$, GND = 0V)

CHARACTERISTIC		TEST CONDITION	V _{EE} (V)	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
Phase Difference Between Input and Output	$\phi_{I/O}$		GND	2.0	—	25	60	—	75	ns
			GND	4.5	—	6	12	—	15	
			GND	6.0	—	5	10	—	13	
			-4.5	4.5	—	4	—	—	—	
Output Enable Time	t_{pZL} t_{pZH}	$R_L = 1\text{k}\Omega$	GND	2.0	—	50	225	—	280	ns
			GND	4.5	—	14	45	—	56	
			GND	6.0	—	12	38	—	48	
			-4.5	4.5	—	14	—	—	—	
Output Disable Time	t_{pLZ} t_{pHZ}	$R_L = 1\text{k}\Omega$	GND	2.0	—	95	225	—	280	ns
			GND	4.5	—	30	45	—	56	
			GND	6.0	—	26	38	—	48	
			-4.5	4.5	—	26	—	—	—	
Control Input Capacitance	C _{IN}		—	—	—	5	10	—	10	pF
Common Terminal Capacitance	C _{IS}		-5.0	5.0	—	11	20	—	20	pF
Switch Terminal Capacitance	C _{OS}		-5.0	5.0	—	7	15	—	15	pF
Feed Through Capacitance	C _{IOS}		-5.0	5.0	—	0.75	2	—	2	pF
Power Dissipation Capacitance	C _{PD}	(Note 1)	GND	5.0	—	67	—	—	—	pF

(Note 1) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 2$$

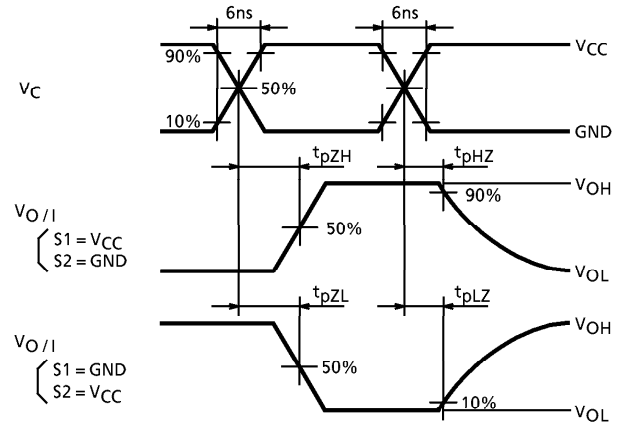
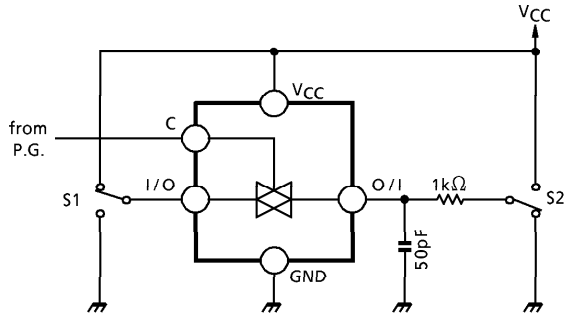
ANALOG SWITCH CHARACTERISTICS (GND = 0V, Ta = 25°C)

CHARACTERISTIC		TEST CONDITION		TYP.	UNIT	
		V_{EE} (V)	V_{CC} (V)			
Sine Wave Distortion (T.H.D)	$R_L = 10k\Omega, C_L = 50pF$ $f_{IN} = 1kHz$	$V_{IN} = 4.0V_{p-p}$	- 2.25	2.25	0.025	%
		$V_{IN} = 8.0V_{p-p}$	- 4.5	4.5	0.02	
		$V_{IN} = 1.1V_{p-p}$	- 6.0	6.0	0.018	
Frequency Response (Switch ON)	f_{MAX} Adjust f_{IN} voltage to obtain 0dBm at V_{OS} Increase f_{IN} until dB Meter reads - 3dB $R_L = 50\Omega, C_L = 10pF$ $f_{IN} = 1MHz, \text{Sine Wave}$	*1	- 2.25	2.25	120	MHz
		*2			95	
		*1	- 4.5	4.5	190	
		*2			150	
		*1	- 6.0	6.0	200	
		*2			190	
Feedthrough Attenuation (Switch OFF)	V_{in} is centered at $(V_{CC}-V_{EE})/2$ Adjust input for 0dBm $R_L = 600\Omega, C_L = 50pF$ $f_{IN} = 1MHz, \text{Sine Wave}$	- 2.25	2.25	- 50	dB	
		- 4.5	4.5	- 50		
		- 6.0	6.0	- 50		
Crosstalk (Control Input to Signal Output)	$R_L = 600\Omega, C_L = 50pF$ $f_{IN} = 1MHz, \text{Square Wave } (t_r = t_f = 6ns)$	- 2.25	2.25	60	mV	
		- 4.5	4.5	140		
		- 6.0	6.0	200		
Crosstalk (Between any switches)	Adjust V_{IN} to obtain 0dBm at Input $R_L = 600\Omega, C_L = 50pF$ $f_{IN} = 1MHz, \text{Sine Wave}$	- 2.25	2.25	- 50	dB	
		- 4.5	4.5	- 50		
		- 6.0	6.0	- 50		

*1 : Input COMMON Terminal, and measured at SWITCH Terminal.
 *2 : Input SWITCH Terminal, and measured at COMMON Terminal.
 (Note): These characteristics are determined by design of device.

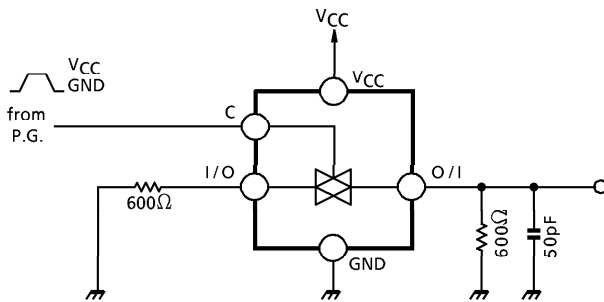
SWITCHING CHARACTERISTICS TEST CIRCUITS

1. t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

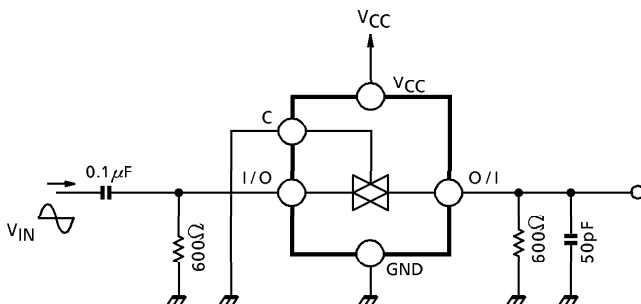


2. CROSS TALK (CONTROL INPUT-SWITCH OUTPUT)

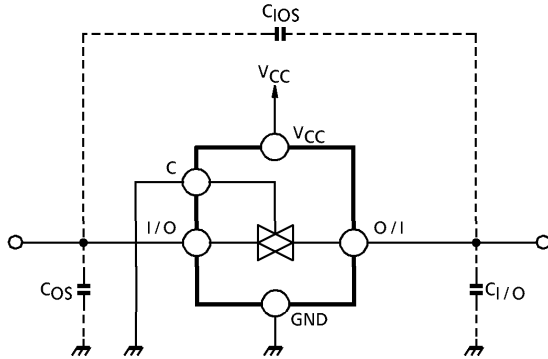
$f_{in} = 1\text{MHz}$, $\text{duty} = 50\%$, $t_r = t_f = 6\text{ns}$



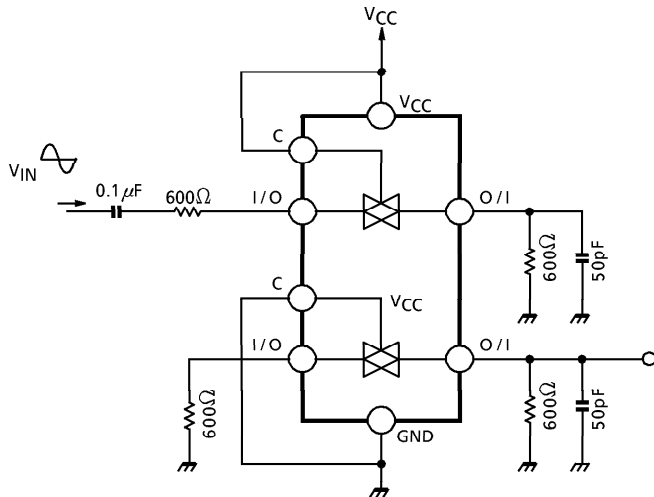
3. FEEDTHROUGH ATTENUATION



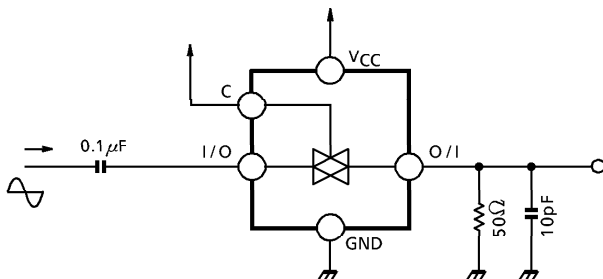
4. Clos, $C_{I/O}$



5. CROSS TALK (BETWEEN ANY TWO SWITCHES)

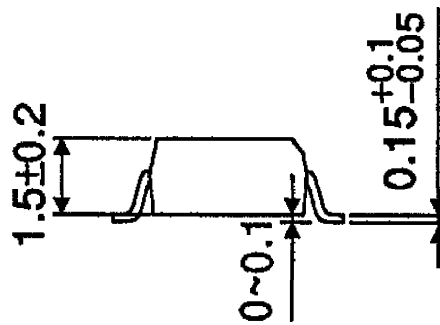
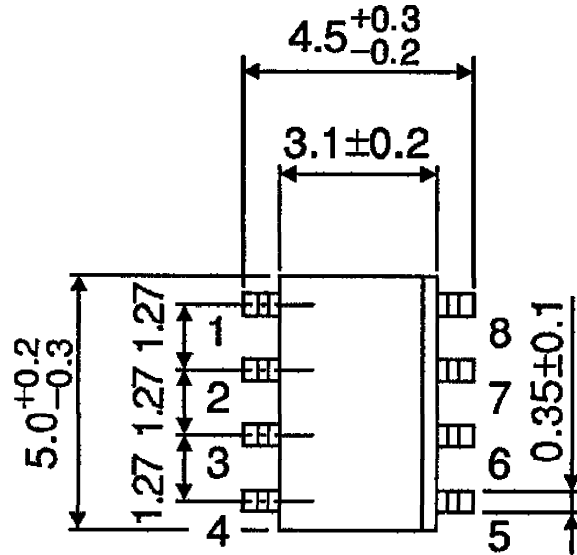


6. FREQUENCY RESPONSE (SWITCH ON)



PACKAGE DIMENSIONS
SOP8-P-1.27

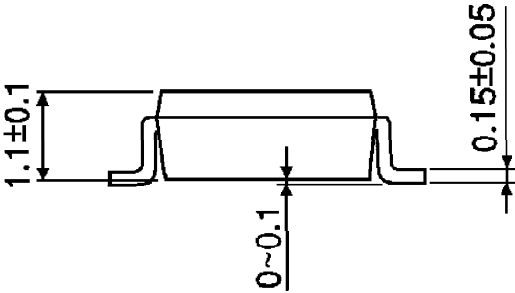
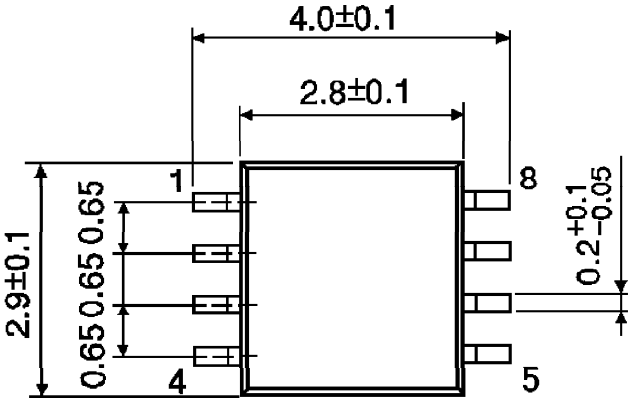
Unit : mm



Weight : 0.05g (Typ.)

PACKAGE DIMENSIONS
SSOP8-P-0.65

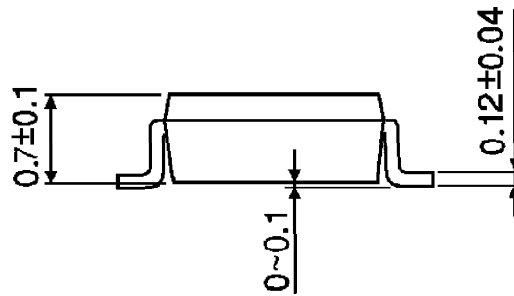
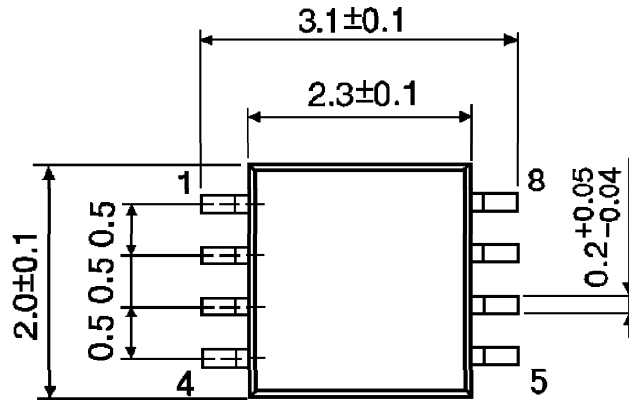
Unit : mm



Weight : 0.02g (Typ.)

PACKAGE DIMENSIONS
SSOP8-P-0.50A

Unit : mm



Weight : 0.01g (Typ.)